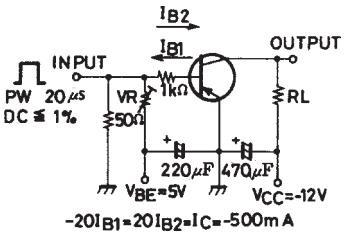
Continued from preceding page.

Electrical Characteristics at Ta=25˚C

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	
[TR]						
Collector Cutoff Current	I_{CBO}	V_{CB}=–20V, I_E=0			–0.1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0			–0.1	µA
DC Current Gain	$h_{FE}1$	V_{CE}=–2V, I_C=–100mA	140		560	
	$h_{FE}2$	V_{CE}=–2V, I_C=–1.5A	65			
Gain-Bandwidth Product	f_T	V_{CE}=–10V, I_C=–50mA		150		MHz
Output Capacitance	Cob	V_{CB}=–10V, f=1MHz		32		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=–1.5A, I_B=–75mA		–0.35	–0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=–1.5A, I_B=–75mA		–0.85	–1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10µA, I_E=0	–30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=–10µA, IC=0	–6			V
Turn-ON Time	t_{on}	See specified Test Circuit		60		ns
Storage Time	tstg	See specified Test Circuit		350		ns
Fall Time	t_f	See specified Test Circuit		25		ns
[SBD]						
Reverse Voltage	V_R	I_R=200µA	50			V
Forward Voltage	V_F	I_F=500mA			0.55	V
Reverse Current	I_R	V_R=25V			50	µA
Interterminal Capacitance	C	V_R=10V, f=1MHz		22		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit			10	ns
Thermal Resistance	Rthj-a	Mounted on ceramic board (250mm²×0.8mm)		120		˚C/W

Switching Time Test Circuit

(TR)



(SBD)